

Number	Hits	Search Text	DB	Time stamp
1	54404	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM	EPO; JPO; DERWENT; IBM_TDB	2003/10/08 10:03
2	8537	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)	EPO; JPO; DERWENT; IBM_TDB	2003/10/08 10:04
3	1695	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)	EPO; JPO; DERWENT; IBM_TDB	2003/10/08 10:04
4	1390	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)	EPO; JPO; DERWENT; IBM_TDB	2003/10/08 10:06
5	879	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)	EPO; JPO; DERWENT; IBM_TDB	2003/10/08 10:16
-	108053	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM	USPAT; US-PGPUB	2003/10/07 18:48
-	93648	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)	USPAT; US-PGPUB	2003/10/07 18:49
-	15472	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)	USPAT; US-PGPUB	2003/10/07 18:50
-	8144	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)	USPAT; US-PGPUB	2003/10/07 18:50
-	7953	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)	USPAT; US-PGPUB	2003/10/07 18:51
-	3360	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))	USPAT; US-PGPUB	2003/10/07 18:51
-	1370	((flash volatile non?volatile (non near3 volatile)) near5 memory) or EEPROM EPROM E2PROM PROM) and (trench recess open\$4 via hole groove contact)) and ((control split select) near5 gate)) and (float\$3 near5 gate)) and (source drain)) and ("ONO" (oxide near5 nitride near5 oxide))) and spacer	USPAT; US-PGPUB	2003/10/07 18:53